PATENT

#2/A
Docket No.:CPH35726-D1 5/13/02
Mollin

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	KUAN-YU FU et al.)
Filed:	Herewith)
For:	MOSFET DEVICE)
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PRELIMINARY AMENDMENT

Assistant Commissioner for Patents Washington, D.C. 20231

Dear Sir:

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Prior to the examination on merits, please amend the above-identified application as follows:

IN THE TITLE:

Please change the title to read:

--MOSFET DEVICE--

IN THE SPECIFICATION:

Please add the following paragraph on page 1, after line 2.

-- CROSS-REFERENCE TO RELATED APPLICATION

This application is a divisional application of, and claims the priority benefit of, U.S. application serial No. 09/382,146 filed on August 24, 1999, which in term is a divisional application of U.S. Patent application No. 09/059,548, filed on April 13, 1998.--

IN THE CLAIMS:

Please cancel claims 1-9 without prejudice and disclaimer.

Please add the following new claims 10-12:

10. A semiconductor structure comprising a substrate having an active region of a first conductivity type including a channel region and a non-channel region surrounding the channel